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June 2014

FDMC8554
N-Channel Power Trench® MOSFET

20V, 16.5A, 5mΩ

Features

- Max $r_{DS(on)}$ = 5mΩ at V_{GS} = 10V, I_D = 16.5A

- Max $r_{DS(on)}$ = 6.4mΩ at V_{GS} = 4.5V, I_D = 14A

- Low Profile - 1mm max in Power 33
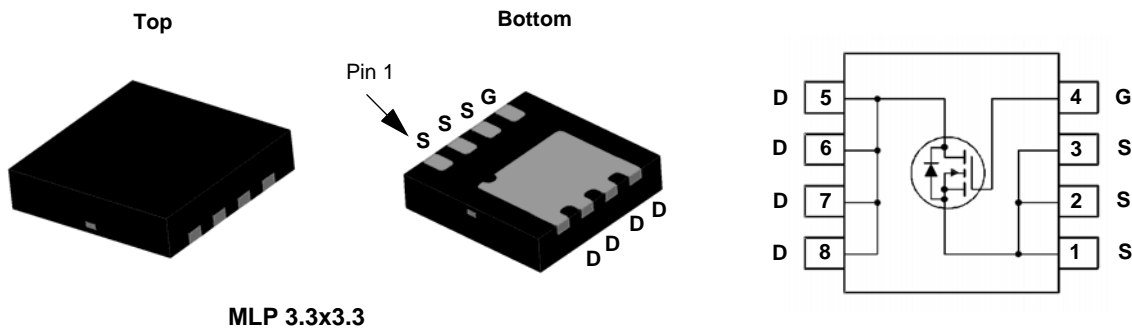
- RoHS Compliant

General Description

This N-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced Power Trench process. It has been optimized for power management applications.

Application

- DC - DC Conversion

Top

Bottom

Pin 1

S S S G

D D D

MLP 3.3x3.3

D	5		4	G
D	6		3	S
D	7		2	S
D	8		1	S

MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			20	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25°C		16.5	A
	-Continuous	T_A = 25°C	(Note 1a)	16.5	
	-Pulsed			36	
P_D	Power Dissipation	T_C = 25°C		41	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	60	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC8554	FDMC8554	Power 33	7''	8mm	3000 units

www.fairchildsemi.com

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		15.7		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16V, V_{GS} = 0V			1	μA
		T_J = 125°C			100	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	1.0	1.8	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-6.1		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 16.5A		3.6	5.0	mΩ
		V_{GS} = 4.5V, I_D = 14A		4.6	6.4	
		V_{GS} = 10V, I_D = 16.5A, T_J = 125°C		5.4	7.1	
g_{FS}	Forward Transconductance	V_{DS} = 5V, I_D = 16.5A		62		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz		2540	3380	pF
C_{oss}	Output Capacitance			795	1060	pF
C_{rss}	Reverse Transfer Capacitance			510	765	pF
R_g	Gate Resistance	f = 1MHz		1.2		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 10V, I_D = 16.5A V_{GS} = 10V, R_{GEN} = 6Ω		13	24	ns
t_r	Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			32	51	ns
t_f	Fall Time			7	14	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{DD} = 10V, I_D = 16.5A		44	62	nC
$Q_{g(TOT)}$	Total Gate Charge at 4.5V			24	34	nC
Q_{gs}	Gate to Source Gate Charge			8.5		nC
Q_{gd}	Gate to Drain "Miller" Charge			10		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 16.5A (Note 2)		0.8	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 16.5A, di/dt = 100A/μs		31	47	ns
Q_{rr}	Reverse Recovery Charge			22	33	nC

Notes:
1: $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
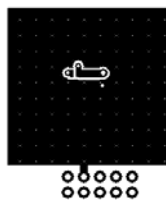
a. 60°C/W when mounted on a 1 in² pad of 2 oz copper

b. 135°C/W when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.

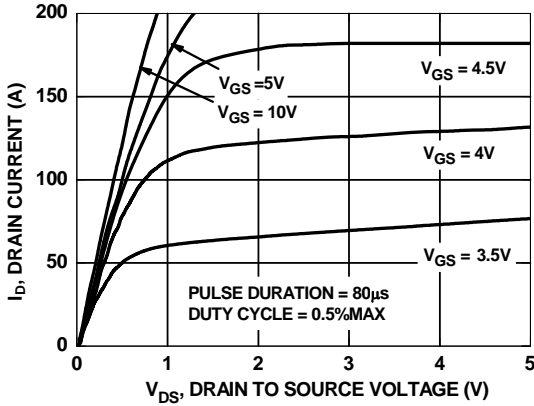## Typical Characteristics $T_J = 25°C$ unless otherwise noted

Figure 1. On-Region Characteristics
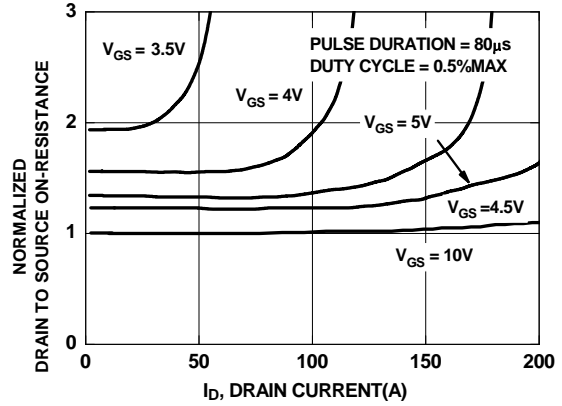

Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage
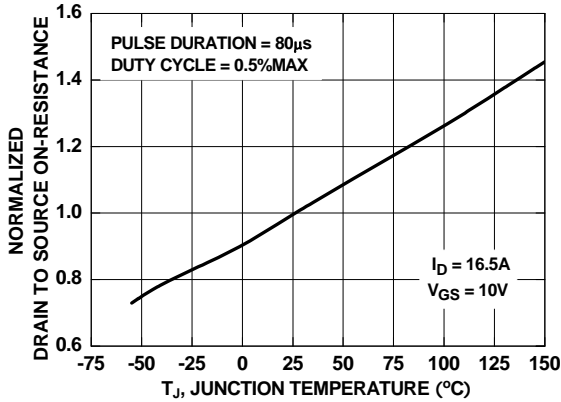

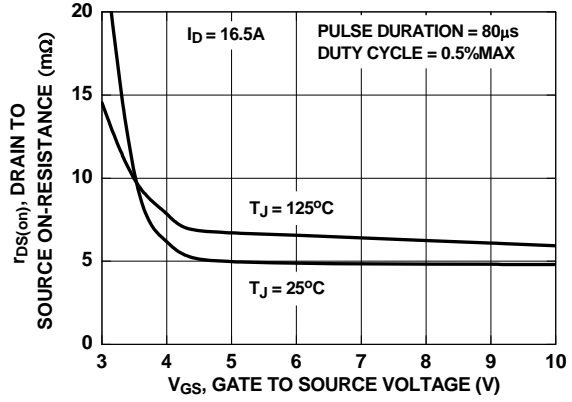**Figure 3. Normalized On-Resistance vs Junction Temperature**
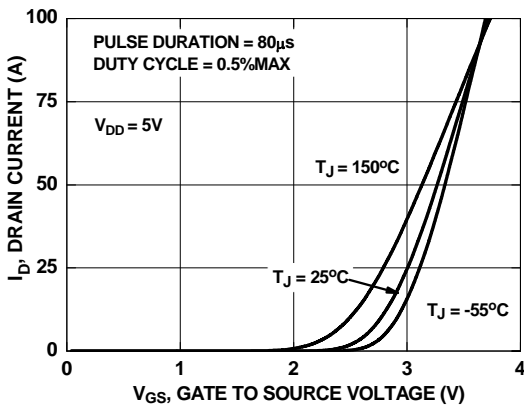

Figure 4. On-Resistance vs Gate to Source Voltage
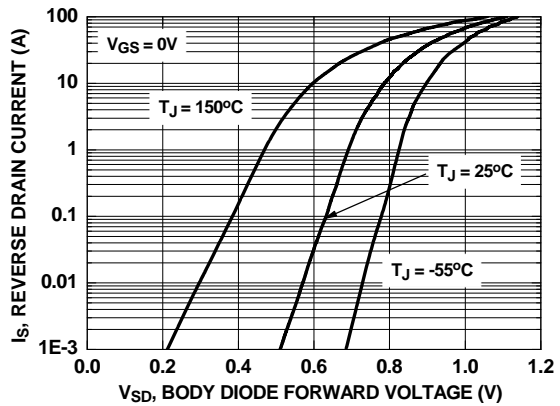

Figure 5. Transfer Characteristics

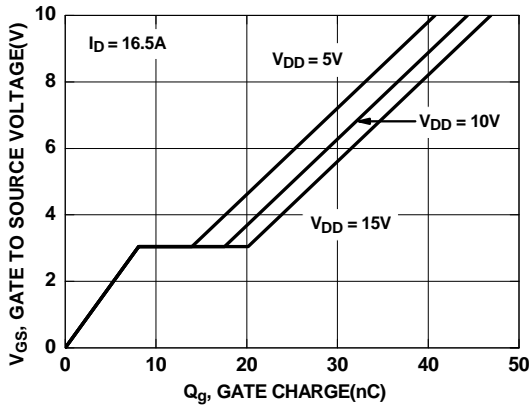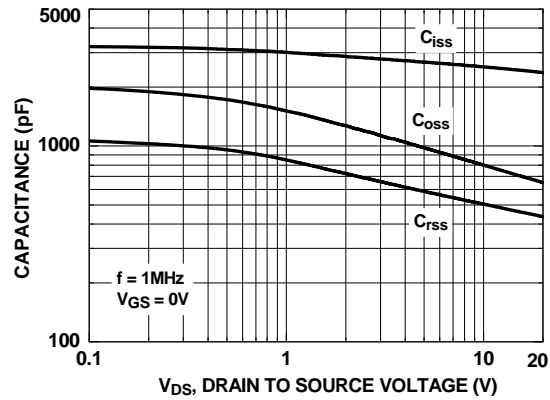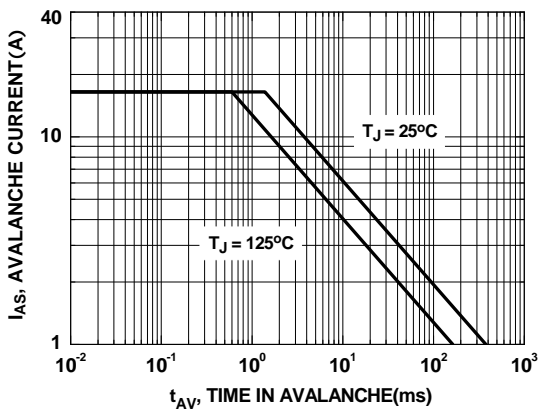**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

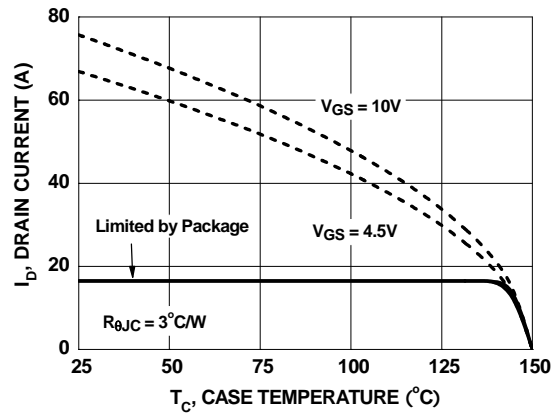## Typical Characteristics T_J = 25°C unless otherwise noted

Figure 7. Gate Charge Characteristics
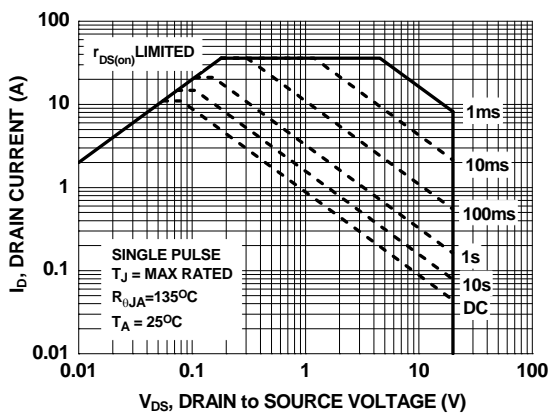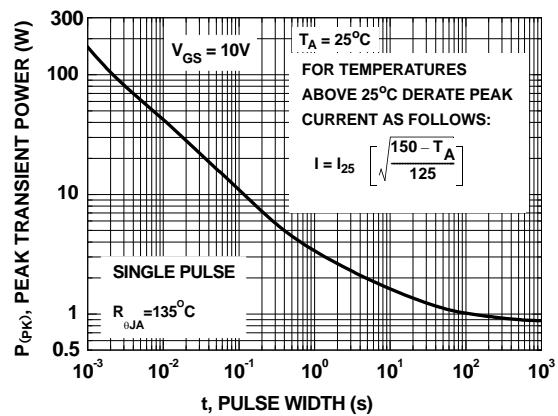

Figure 8. Capacitance vs Drain to Source Voltage

Figure 9. Unclamped Inductive Switching Capability

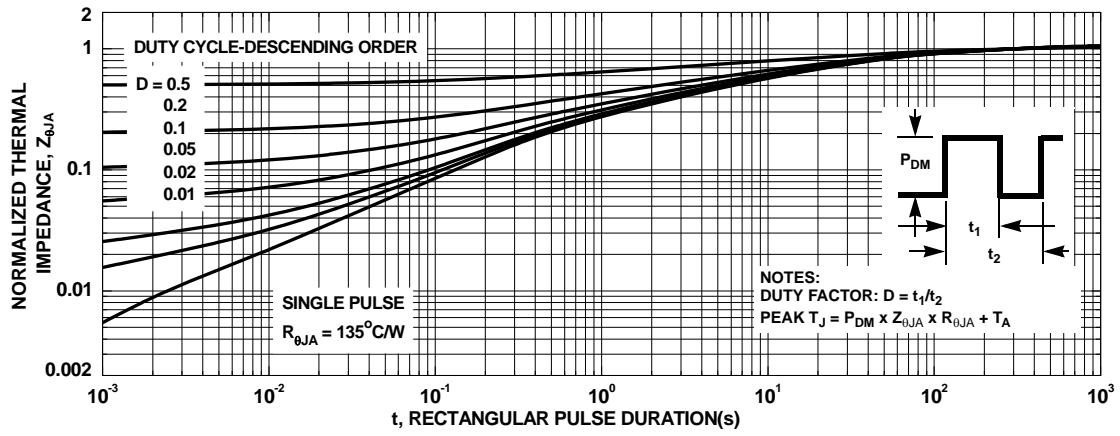Figure 10. Maximum Continuous Drain Current vs Ambient Temperature
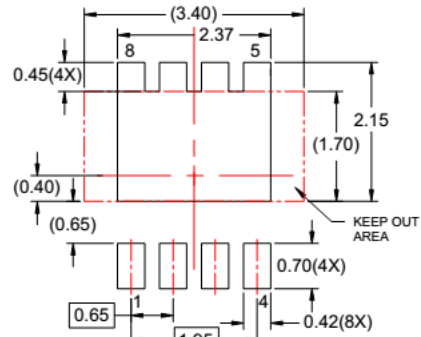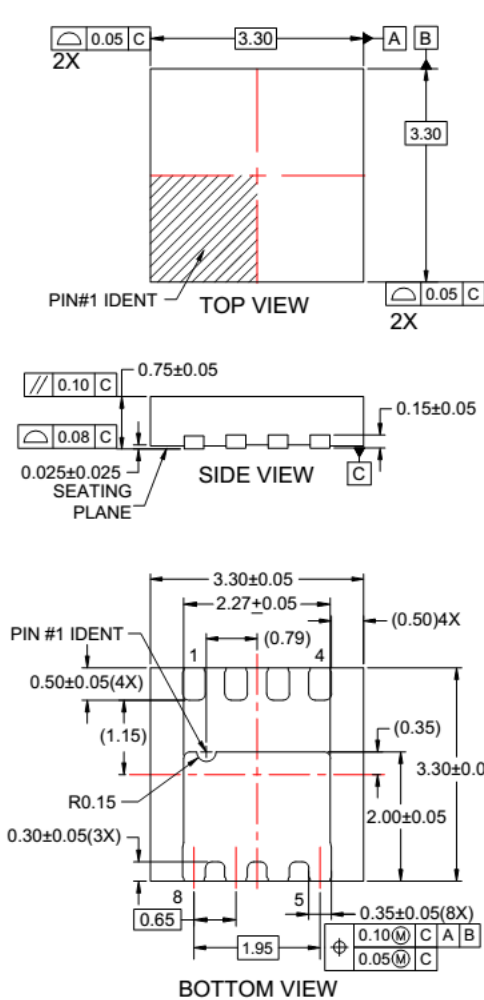

Figure 11. Forward Bias Safe Operating Area

Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

Figure 13. Transient Thermal Response Curve

Dimensional Outline and Pad Layout

2X   ⌓ 0.05 C

3.30

A B

3.30

PIN#1 IDENT

TOP VIEW

2X   ⌓ 0.05 C

(3.40)
2.37

8   5

0.45(4X)

2.15
(1.70)

(0.40)

(0.65)

KEEP OUT
AREA

0.70(4X)

0.65   1   4

0.42(8X)

1.95

RECOMMENDED LAND PATTERN

0.75±0.05

∥ 0.10 C

⌓ 0.08 C

0.15±0.05

0.025±0.025
SEATING
PLANE

SIDE VIEW

C

NOTES:

A. DOES NOT CONFORM TO JEDEC
   REGISTRATION MO-229

B. DIMENSIONS ARE IN MILLIMETERS.

C. DIMENSIONS AND TOLERANCES PER
   ASME Y14.5M, 2009.

D. LAND PATTERN RECOMMENDATION IS
   EXISTING INDUSTRY LAND PATTERN.

E. DRAWING FILENAME: MKT-MLP08Srev3.

3.30±0.05
2.27+0.05
(0.79)

PIN #1 IDENT

1   4

(0.50)4X

0.50±0.05(4X)

(1.15)

(0.35)

3.30±0.05

R0.15

2.00±0.05

0.30±0.05(3X)

8   5

0.65

0.35±0.05(8X)

⊕ 0.10 Ⓜ C A B

1.95

0.05 Ⓜ C

BOTTOM VIEW

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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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